

Caims 1-12. (Cancelled)

Claim 13. (Original) A semiconductor transistor comprising:

a gate pattern formed on a semiconductor substrate;

an L-shaped third spacer having a horizontal protruding portion, the third spacer being formed on a sidewall surface of the gate pattern;

an L-shaped fourth spacer having a vertical sidewall between a vertical sidewall of the L-shaped third spacer and the gate pattern and a horizontal protruding portion between the protruding portion of the L-shaped third spacer and the substrate;

a high-concentration junction area formed in the substrate beyond the L-shaped third spacer;

a low-concentration junction area formed in the substrate under the horizontal protruding portion of the L-shaped third spacer; and

a medium-concentration junction area positioned between the high- and low-concentration junction areas.

Claim 14. (Original) The semiconductor transistor as claimed in claim 13, wherein the medium- and low-concentration junction areas are formed under the protruding portion of the L-shaped third spacer.

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Claim 15. (Original) The semiconductor transistor as claimed in claim 13, wherein the L-shaped fourth spacer is made of silicon oxide.

Claim 16. (Original) The semiconductor transistor as claimed in claim 13, wherein the L-shaped third spacer is made of material having an etch selectivity with respect to the L-shaped fourth spacer.

Claims 17-25. (Cancelled)